Silicon NPN Power Transistors 2SD2340

DESCRIPTION

·With TO-3PN package
·DARLINGTON
·High DC current gain

APPLICATIONS

·Audio ,regulator and general purpose

PINNING

PIN	DESCRIPTION
1	Base
2	Collector;connected to mounting base
3	Emitter

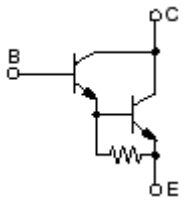

Fig.1 simplified outline (TO-3PN) and symbol

Absolute maximum ratings(Ta=□)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage	Open emitter	130	V
V_{CEO}	Collector-emitter voltage	Open base	110	V
V_{EBO}	Emitter-base voltage	Open collector	5	V
I_C	Collector current		6	A
P_C	Collector power dissipation	T_C=25□	50	W
		T_a=25□	2.5	
T_j	Junction temperature		150	□
T_{stg}	Storage temperature		-55~150	□

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CHARACTERISTICS

Tj=25□ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CEO}$	Collector-emitter breakdown voltage	I_C=30mA ;I_B=0	110			V
V_{CEsat}	Collector-emitter saturation voltage	I_C=5A ;I_B=5mA			2.5	V
V_{BEsat}	Base-emitter saturation voltage	I_C=5A ;I_B=5mA			3.0	V
I_{CBO}	Collector cut-off current	V_{CB}=130V; I_E=0			100	μA
I_{CEO}	Collector cut-off current	V_{CE}=110V I_B=0			100	μA
I_{EBO}	Emitter cut-off current	V_{EB}=5V; I_C=0			100	μA
h_{FE}	DC current gain	I_C=3A ; V_{CE}=5V	5000			
f_T	Transition frequency	I_C=0.5A ; V_{CE}=10V		20		MHz

PACKAGE OUTLINE

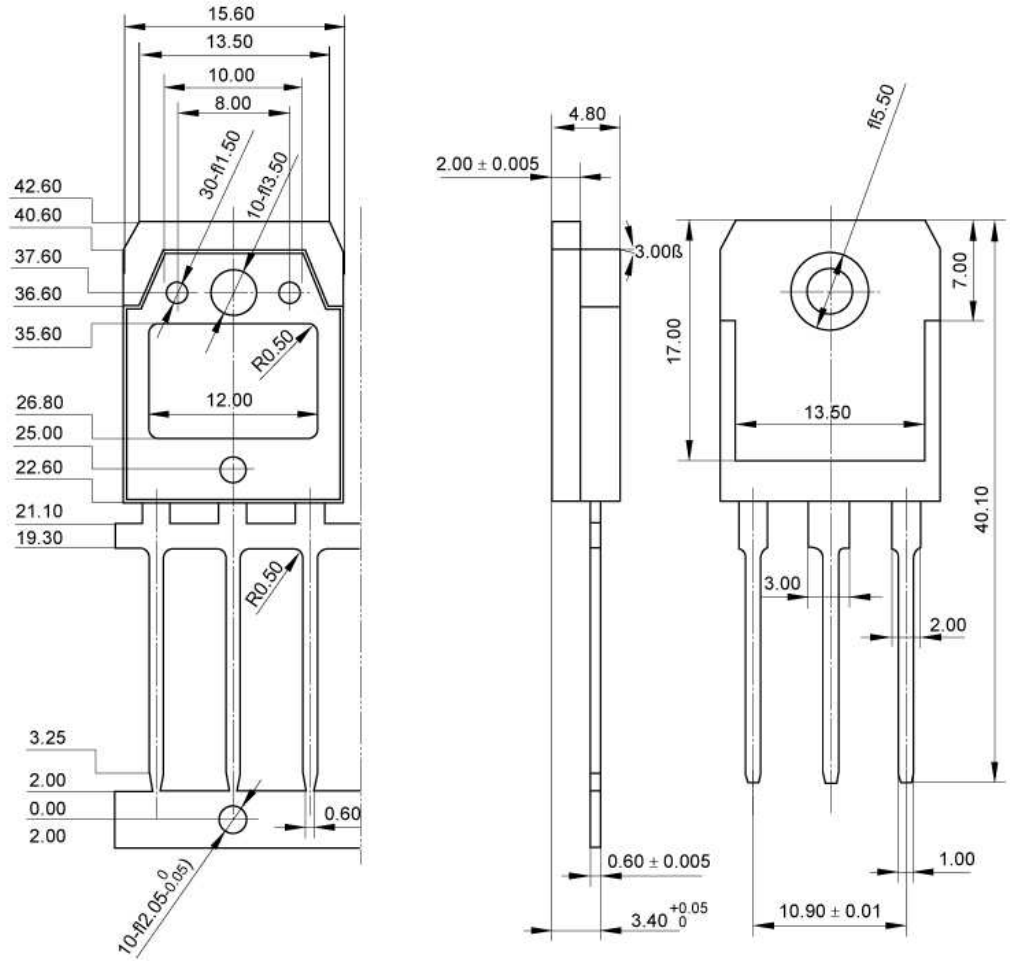

Fig.2 outline dimensions (unindicated tolerance:±0.1mm)